



UPC8026

Preliminary

Power MOSFET

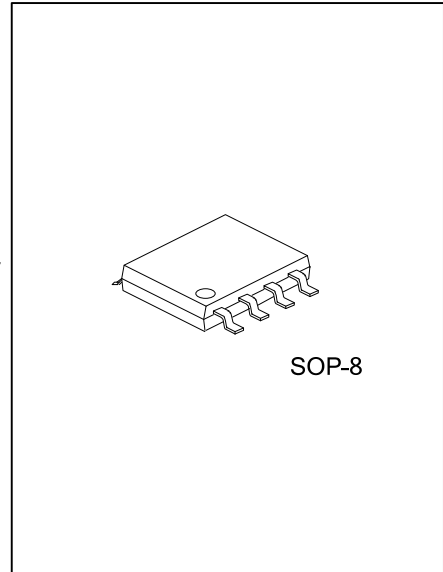
30V, 13A N-CHANNEL POWER MOSFET

DESCRIPTION

The UTC **UPC8026** is an N-channel enhancement mode power MOSFET using UTC's advanced technology to provide customers with a minimum on-state resistance, low leakage current and high forward transfer admittance.

FEATURES

- * $V_{DS} = 30V, I_D = 13A$
- * $R_{DS(ON)} = 0.0051\Omega @ V_{GS} = 10V,$
 $R_{DS(ON)} = 0.0075\Omega @ V_{GS} = 4.5V$
- * High forward transfer admittance: $|Y_{fs}| = 30S$
- * Low leakage current: $I_{DSS} < 10\mu A @ V_{DS} = 30V$



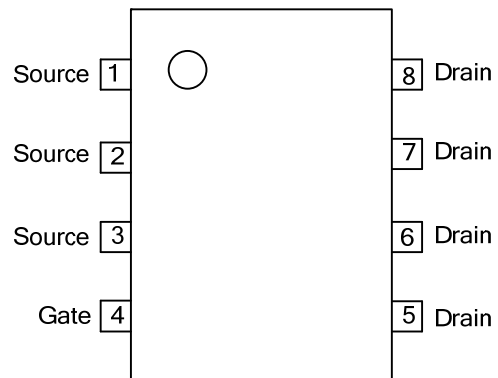
ORDERING INFORMATION

Ordering Number		Package	Packing
Lead Free	Halogen Free		
UPC8026L-S08-R	UPC8026G-S08-R	SOP-8	Tape Reel

Note: Pin Assignment: G: Gate D: Drain S: Source

<p>UPC8026L-S08-R</p> <ul style="list-style-type: none"> (1) Packing Type (2) Package Type (3) Lead Free 	<ul style="list-style-type: none"> (1) R: Tape Reel, T: Tube (2) S08: SOP-8 (3) G: Halogen Free, L: Lead Free
---	--

■ PIN CONFIGURATION



■ ABSOLUTE MAXIMUM RATINGS ($T_A=25^\circ\text{C}$, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V_{DSS}	30	V
Gate-Source Voltage		V_{GSS}	± 20	V
Drain-Gate Voltage ($R_{GS}=20\text{k}\Omega$)		V_{DGR}	30	V
Drain Current	Continuous (Note 2)	I_D	13	A
	Pulsed (Note 2)	I_{DM}	52	A
Avalanche Current		I_{AR}	13	A
Avalanche Energy	Single Pulsed (Note 4)	E_{AS}	44	mJ
	Repetitive (Note 3, 5)	E_{AR}	0.048	mJ
Power Dissipation (Nota 3)		P_D	1.9	W
Channel Temperature		T_{CH}	150	$^\circ\text{C}$
Storage Temperature		T_{STG}	-55~+150	$^\circ\text{C}$

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Ensure that the channel temperature does not exceed 150°C .
3. Device mounted on a glass-epoxy board FR-4, $25.4 \times 25.4 \times 0.8$ (unit: mm)
4. $V_{DD}=24\text{V}$, $T_{CH}=25^\circ\text{C}$ (initial), $L=0.2\text{mH}$, $I_{AR}=13\text{A}$
5. Repetitive rating: pulse width limited by max channel temperature

■ THERMAL CHARACTERISTICS

PARAMETER	SYMBOL	RATINGS	UNIT
Junction to Ambient (Nota 3)	θ_{JA}	65.8	$^\circ\text{C}/\text{W}$

■ ELECTRICAL CHARACTERISTICS (T_A=25°C)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT	
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage	V _{(BR)DSS}	I _D =10mA, V _{GS} =0V	30			V	
	V _{(BR)DSX}	I _D =10mA, V _{GS} =-20 V	10				
Drain-Source Leakage Current	I _{DSS}	V _{DS} =30V, V _{GS} =0 V			10	μA	
Gate- Source Leakage Current	I _{GSS}	V _{GS} =+20V, V _{DS} =0V			+100	nA	
		V _{GS} =-20V, V _{DS} =0V			-100	nA	
ON CHARACTERISTICS							
Gate Threshold Voltage	V _{GS(TH)}	V _{DS} =10 V, I _D =1mA	1.3		2.5	V	
Static Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =4.5V, I _D =6.5A		7.5	10	mΩ	
		V _{GS} =10V, I _D =6.5A		5.1	6.6		
Forward Transfer Admittance	Y _{FS}	V _{DS} =10V, I _D =6.5A	15	30		S	
DYNAMIC PARAMETERS							
Input Capacitance	C _{ISS}	V _{DS} =10V, V _{GS} =0V, f=1MHz		1800		pF	
Output Capacitance	C _{OSS}				570		pF
Reverse Transfer Capacitance	C _{RSS}				370		pF
SWITCHING PARAMETERS							
Total Gate Charge	Q _G	V _{DD} ≈24V, V _{GS} =10V, I _D =13 A		42		nC	
Gate to Source Charge	Q _{GS}			6.5		nC	
Gate to Drain Charge	Q _{GD}			14		nC	
Turn-ON Delay Time	t _{D(ON)}			28		ns	
Rise Time	t _R				15		ns
Turn-OFF Delay Time	t _{D(OFF)}				54		ns
Fall-Time	t _F						
					21		ns
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS							
Drain Reverse Current	Pulse (Note 1)	I _{DRP}			52	A	
Forward Voltage (Diode)		V _{DSF}	I _{DR} =13A, V _{GS} =0V		-1.2	V	

Note: 1. Ensure that the channel temperature does not exceed 150°C.

UTC assumes no responsibility for equipment failures that result from using products at values that exceed, even momentarily, rated values (such as maximum ratings, operating condition ranges, or other parameters) listed in products specifications of any and all UTC products described or contained herein. UTC products are not designed for use in life support appliances, devices or systems where malfunction of these products can be reasonably expected to result in personal injury. Reproduction in whole or in part is prohibited without the prior written consent of the copyright owner. The information presented in this document does not form part of any quotation or contract, is believed to be accurate and reliable and may be changed without notice.